Appl. No. 10/709,666
Amdt. dated November 09, 2005
Reply to Office action of October 18, 2005

Amendments to the Specification:

Please replace Abstract of Disclosure with the following context:

A method for programming a single-bit storage nonvolatile memory cell includes the
5   steps of: providing a single-bit storage nonvolatile memory cell having a channel region
between a left bit line and a right bit line, a composite dielectric layer for storing digital
data, and a word line overlying the composite dielectric layer; performing a left side
electron injection on the single-bit storage nonvolatile memory cell by applying a
relatively high word line voltage $(V_{WL, HIGH})$ to the word line, applying a relatively high
10   left bit line voltage $(V_{LBL, HIGH})$ to the left bit line, and applying a relatively low right bit
line voltage $(V_{RBL, LOW})$ to the right bit line; and performing a right side electron injection
~~on the single-bit storage nonvolatile memory cell~~ by applying the relatively high word
line voltage $(V_{WL, HIGH})$ to the word line, applying a relatively low left bit line voltage
$(V_{LBL, LOW})$ to the left bit line, and applying a relatively high right bit line voltage $(V_{RBL,}$
15   $_{HIGH})$ to the right bit line.

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